

L Number	Hits	Search Text	DB	Time stamp
-	997	257/57	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/04/22 11:48
-	1675	257/59	US-PGPUB; EPO; JPO; DERWENT;	2002/04/17 17:24
-	1323	257/72	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/04/17 17:10
-	80	438/609	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/04/17 17:10
-	682	438/149	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/04/17 17:11
-	96	438/341	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/04/17 17:11
-	173	437/181	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/04/17 17:11
-	349	438/48	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/04/17 17:11
-	1641	438/128	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/04/17 17:12
-	863	438/151	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/04/17 17:13
-	207	438/157	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/04/17 17:13
-	636	438/166	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/04/17 17:13
-	889	257/59 and transparent and (thin adj film adj transistor)	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/10/23 09:19
-	1	257/581 and transparent and (thin adj film adj transistor)	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/04/17 17:38

	67	257/59 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/17 17:55
	45	257/72 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 17:49
	13	257/57 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 15:12
	1	257/359 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/17 17:55
	5	437/181 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/17 17:56
	1	438/609 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/17 17:56
	8	438/149 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/17 17:56
	1	438/48 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/17 17:56
	1	438/128 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/18 07:40
	11	438/151 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/17 18:21
	3	438/157 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/17 18:09
	4	438/166 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/17 18:22
	289	el and transparent and (thin adj film and transistor) and (257/\$.ccls. or 438/\$.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 19:01
	1	"6235561".PN.	USPAT	2002/04/18 11:45
	1	"5446562".PN.	USPAT	2002/04/18 15:01

	262	257/57 and ((silicon adj oxide) same thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 18:36
	6	257/57 and ((protective adj insulating adj film) same thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/18 17:57
	12	257/59 and ((protective adj insulating adj film) same thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/18 16:02
	10	257/72 and ((protective adj insulating adj film) same thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/22 13:16
	2	257/57 and ((protective adj insulating adj film) same defect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/22 15:11
	6	257/59 and ((protective adj insulating adj film) same defect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/18 17:59
	3	257/72 and ((protective adj insulating adj film) same defect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/18 17:59
	7	TFT and ((protective adj insulating adj film) same (amorphous adj silicon)) and (257/\$.cccls. or 438/\$.cccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/22 12:58
	6	TFT and ((protective adj insulating adj film) WITH (amorphous adj silicon)) and (257/\$.cccls. or 438/\$.cccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/22 12:59
	6	257/72 and ((protective adj insulating adj film) same amorphous)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/22 13:17
	10	257/59 and ((protective adj insulating adj film) same amorphous)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/22 13:17
	8	257/57 and ((protective adj insulating adj film) same amorphous)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/22 13:17
	38	257/72 and ((silicon adj oxide) same defect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/22 15:12
	37	257/59 and ((silicon adj oxide) same defect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/22 15:12

	24	257/57 and ((silicon adj oxide) same defect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 15:19
	837	257/72 and transparent and (thin adj film adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 11:17
	51	257/72 and transparent and (thin adj film adj transistor) and (thickness near (silicon adj nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 11:37
	1	257/72 and transparent and (thin adj film adj transistor) and ((protective adj insulating adj film) near2 ("100" nm))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 11:40
	11	257/72 and transparent and (thin adj film adj transistor) and ((protective adj insulating adj film) with ("100" nm))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 17:45
	1	"6046479".PN.	USPAT	2002/10/23 13:32
	5	257/59 and ((protective adj insulating adj film) with defect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 15:50
	2	257/72 and ((protective adj insulating adj film) with defect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 15:49
	6	257/\$.ccls. and ((protective adj insulating adj film) with defect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 16:47
	2	438/\$.ccls. and ((protective adj insulating adj film) with defect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 16:06
	17	(protective adj insulating adj film) with defect	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 16:10
	6	257/72 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (alignment adj layer) and (counter adj substrate) and (counter adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 18:34
	566	(organic adj 'EL') and (thin adj film adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 19:02
	114	(organic adj 'EL') and (thin adj film adj transistor) and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 19:06
	7	(organic adj 'EL') and (cathode adj layer) and (anode adj layer) and (thin adj film adj transistor) and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 19:07

-	7	257/\$.ccls. and ((amorphous adj film) with oxidation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/01 16:58
-	7	257/\$.ccls. and (oxidation with (amorphous adj film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/01 17:10
-	1	(surface adj oxidation) near2 (amorphous adj film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/01 17:44
-	20	(thermal adj oxidation) SAME (amorphous adj film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/10 16:35
-	102	(surface near2 (amorphous adj silicon)) with oxidation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/03 10:09
-	74	(surface near2 (amorphous adj silicon)) near5 oxidation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/03 10:44
-	3	nitride with ((surface near2 (amorphous adj silicon)) near5 oxidation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/03 10:59
-	1	nitride near5 ((surface near2 (amorphous adj silicon)) near5 oxidation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/03 10:59
-	19	surface with (amorphous adj film) with oxidation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/11 08:33
-	245	438/150	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/11 08:38
-	193	438/150 and (TFT or (thin adj film adj transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/11 10:24
-	787	438/151 and (TFT or (thin adj film adj transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/11 10:26
-	108	438/151 and (TFT or (thin adj film adj transistor)) and (surface with (amorphous adj silicon) with (oxide or oxidation))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/11 10:30
-	233	438/151 and (TFT or (thin adj film adj transistor)) and ((amorphous adj silicon) with (oxide or oxidation))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/11 10:32

-	113	438/151 and (TFT or (thin adj film adj transistor)) and ((amorphous adj silicon) with (oxide or oxidation)) and polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/11 10:33
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